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Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8349ezuagdb

- Complies with USB specification Rev. 2.0
- Can operate as a stand-alone USB device
 - One upstream facing port
 - Six programmable USB endpoints
- Can operate as a stand-alone USB host controller
 - USB root hub with one downstream-facing port
 - Enhanced host controller interface (EHCI) compatible
 - High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
- External PHY with UTMI, serial and UTMI+ low-pin interface (ULPI)
- Universal serial bus (USB) multi-port host controller
 - Can operate as a stand-alone USB host controller
 - USB root hub with one or two downstream-facing ports
 - Enhanced host controller interface (EHCI) compatible
 - Complies with *USB Specification Rev. 2.0*
 - High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
 - Direct connection to a high-speed device without an external hub
 - External PHY with serial and low-pin count (ULPI) interfaces
- Local bus controller (LBC)
 - Multiplexed 32-bit address and data operating at up to 133 MHz
 - Eight chip selects for eight external slaves
 - Up to eight-beat burst transfers
 - 32-, 16-, and 8-bit port sizes controlled by an on-chip memory controller
 - Three protocol engines on a per chip select basis:
 - General-purpose chip select machine (GPCM)
 - Three user-programmable machines (UPMs)
 - Dedicated single data rate SDRAM controller
 - Parity support
 - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Programmable interrupt controller (PIC)
 - Functional and programming compatibility with the MPC8260 interrupt controller
 - Support for 8 external and 35 internal discrete interrupt sources
 - Support for 1 external (optional) and 7 internal machine checkstop interrupt sources
 - Programmable highest priority request
 - Four groups of interrupts with programmable priority
 - External and internal interrupts directed to host processor
 - Redirects interrupts to external $\overline{\text{INTA}}$ pin in core disable mode.
 - Unique vector number for each interrupt source

- ² Typical power is based on a voltage of $V_{DD} = 1.2$ V, a junction temperature of $T_J = 105^\circ\text{C}$, and a Dhrystone benchmark application.
- ³ Thermal solutions may need to design to a value higher than typical power based on the end application, T_A target, and I/O power.
- ⁴ Maximum power is based on a voltage of $V_{DD} = 1.2$ V, worst case process, a junction temperature of $T_J = 105^\circ\text{C}$, and an artificial smoke test.
- ⁵ Typical power is based on a voltage of $V_{DD} = 1.3$ V, a junction temperature of $T_J = 105^\circ\text{C}$, and a Dhrystone benchmark application.
- ⁶ Maximum power is based on a voltage of $V_{DD} = 1.3$ V, worst case process, a junction temperature of $T_J = 105^\circ\text{C}$, and an artificial smoke test.

Table 5 shows the estimated typical I/O power dissipation for MPC8349EA.

Table 5. MPC8349EA Typical I/O Power Dissipation

Interface	Parameter	GV_{DD} (1.8 V)	GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization 2.5 V $R_s = 20\ \Omega$ $R_t = 50\ \Omega$ 2 pair of clocks	200 MHz, 32 bits	0.31	0.42	—	—	—	W	—
	200 MHz, 64 bits	0.42	0.55	—	—	—	W	—
	266 MHz, 32 bits	0.35	0.5	—	—	—	W	—
	266 MHz, 64 bits	0.47	0.66	—	—	—	W	—
	300 MHz, 32 bits	0.37	0.54	—	—	—	W	—
	300 MHz, 64 bits	0.50	0.7	—	—	—	W	—
	333 MHz, 32 bits	0.39	0.58	—	—	—	W	—
	333 MHz, 64 bits	0.53	0.76	—	—	—	W	—
	400 MHz, 32 bits	0.44	—	—	—	—	—	—
	400 MHz, 64 bits	0.59	—	—	—	—	—	—
PCI I/O load = 30 pF	33 MHz, 64 bits	—	—	0.08	—	—	W	—
	66 MHz, 64 bits	—	—	0.14	—	—	W	—
	33 MHz, 32 bits	—	—	0.04	—	—	W	Multiply by 2 if using 2 ports.
	66 MHz, 32 bits	—	—	0.07	—	—	W	
Local bus I/O load = 25 pF	133 MHz, 32 bits	—	—	0.27	—	—	W	—
	83 MHz, 32 bits	—	—	0.17	—	—	W	—
	66 MHz, 32 bits	—	—	0.14	—	—	W	—
	50 MHz, 32 bits	—	—	0.11	—	—	W	—
TSEC I/O load = 25 pF	MII	—	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	—	0.06	—	W	
	RGMII or RTBI	—	—	—	—	0.04	W	
USB	12 MHz	—	—	0.01	—	—	W	Multiply by 2 if using 2 ports.
	480 MHz	—	—	0.2	—	—	W	
Other I/O	—	—	—	0.01	—	—	W	—

4 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the device.

4.1 DC Electrical Characteristics

Table 6 provides the clock input (CLKIN/PCI_SYNC_IN) DC timing specifications for the MPC8349EA.

Table 6. CLKIN DC Timing Specifications

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V_{IH}	2.7	$OV_{DD} + 0.3$	V
Input low voltage	—	V_{IL}	−0.3	0.4	V
CLKIN input current	$0\text{ V} \leq V_{IN} \leq OV_{DD}$	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	$0\text{ V} \leq V_{IN} \leq 0.5\text{ V}$ or $OV_{DD} - 0.5\text{ V} \leq V_{IN} \leq OV_{DD}$	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	$0.5\text{ V} \leq V_{IN} \leq OV_{DD} - 0.5\text{ V}$	I_{IN}	—	±50	μA

4.2 AC Electrical Characteristics

The primary clock source for the MPC8349EA can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Table 7 provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the device.

Table 7. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	—	—	66	MHz	1, 6
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN/PCI_CLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	2.3	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:

- Caution:** The system, core, USB, security, and TSEC must not exceed their respective maximum or minimum operating frequencies.
- Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 and 2.7 V.
- Timing is guaranteed by design and characterization.
- This represents the total input jitter—short term and long term—and is guaranteed by design.
- The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be < 500 kHz at −20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.
- Spread spectrum clocking is allowed with 1% input frequency down-spread at maximum 50 KHz modulation rate regardless of input frequency.

Table 11 lists the PLL and DLL lock times.

Table 11. PLL and DLL Lock Times

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	μs	—
DLL lock times	7680	122,880	csb_clk cycles	1, 2

Notes:

1. DLL lock times are a function of the ratio between the output clock and the coherency system bus clock (csb_clk). A 2:1 ratio results in the minimum and an 8:1 ratio results in the maximum.
2. The csb_clk is determined by the CLKIN and system PLL ratio. See [Section 19, “Clocking.”](#)

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8349EA. Note that DDR SDRAM is $GV_{DD}(\text{typ}) = 2.5 \text{ V}$ and DDR2 SDRAM is $GV_{DD}(\text{typ}) = 1.8 \text{ V}$. The AC electrical specifications are the same for DDR and DDR2 SDRAM.

NOTE

The information in this document is accurate for revision 3.0 silicon and later. For information on revision 1.1 silicon and earlier versions see the *MPC8349E PowerQUICC II Pro Integrated Host Processor Hardware Specifications*. See [Section 22.1, “Part Numbers Fully Addressed by This Document,”](#) for silicon revision level determination.

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

Table 12 provides the recommended operating conditions for the DDR2 SDRAM component(s) of the MPC8349EA when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 12. DDR2 SDRAM DC Electrical Characteristics for $GV_{DD}(\text{typ}) = 1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	-9.9	9.9	μA	4
Output high current ($V_{OUT} = 1.420 \text{ V}$)	I_{OH}	-13.4	—	mA	—

Table 15 provides the DDR capacitance when $GV_{DD}(\text{typ}) = 2.5 \text{ V}$.

Table 15. DDR SDRAM Capacitance for $GV_{DD}(\text{typ}) = 2.5 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. $GV_{DD} = 2.5 \text{ V} \pm 0.125 \text{ V}$, $f = 1 \text{ MHz}$, $T_A = 25^\circ\text{C}$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 16 provides the current draw characteristics for MV_{REF} .

Table 16. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Note
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:

1. The voltage regulator for MV_{REF} must supply up to 500 μA current.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

Table 17 provides the input AC timing specifications for the DDR2 SDRAM when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 17. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of $1.8 \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	$MV_{REF} - 0.25$	V	—
AC input high voltage	V_{IH}	$MV_{REF} + 0.25$	—	V	—

Table 18 provides the input AC timing specifications for the DDR SDRAM when $GV_{DD}(\text{typ}) = 2.5 \text{ V}$.

Table 18. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions with GV_{DD} of $2.5 \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	$MV_{REF} - 0.31$	V	—
AC input high voltage	V_{IH}	$MV_{REF} + 0.31$	—	V	—

Table 19 provides the input AC timing specifications for the DDR SDRAM interface.

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of $(1.8 \text{ or } 2.5 \text{ V}) \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC/MDM	t_{CISKEW}			ps	1, 2
400 MHz		–600	600		3
333 MHz		–750	750		—
266 MHz		–750	750		—
200 MHz		–750	750		—

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW} . This can be determined by the equation: $t_{DISKEW} = \pm (T/4 - \text{abs}(t_{CISKEW}))$; where T is the clock period and $\text{abs}(t_{CISKEW})$ is the absolute value of t_{CISKEW} .
3. This specification applies only to the DDR interface.

Figure 5 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

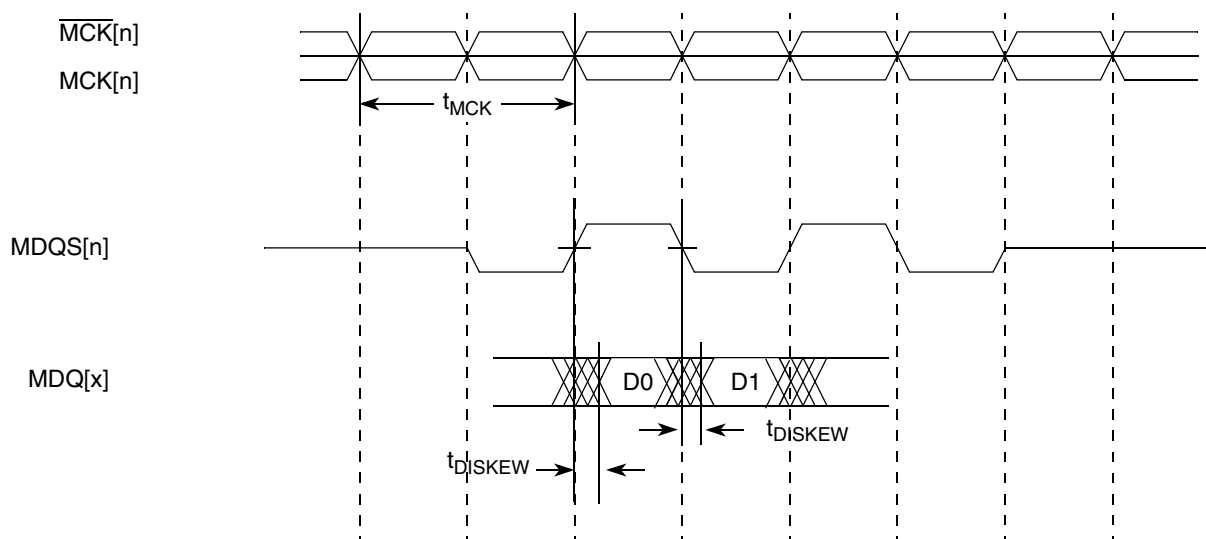


Figure 5. DDR Input Timing Diagram

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications (continued)At recommended operating conditions with GV_{DD} of $(1.8 \text{ or } 2.5 \text{ V}) \pm 5\%$.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	-0.6	0.6	ns	6

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output goes invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are set up (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/ \overline{MCK} referenced measurements are made from the crossing of the two signals $\pm 0.1 \text{ V}$.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/ \overline{MCK} , \overline{MCS} , and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.
4. t_{DDKHHM} follows the symbol conventions described in note 1. For example, t_{DDKHHM} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHHM} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register and is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters are set to the same adjustment value. See the *MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual* for the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK(n) at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Figure 6 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHHM}).

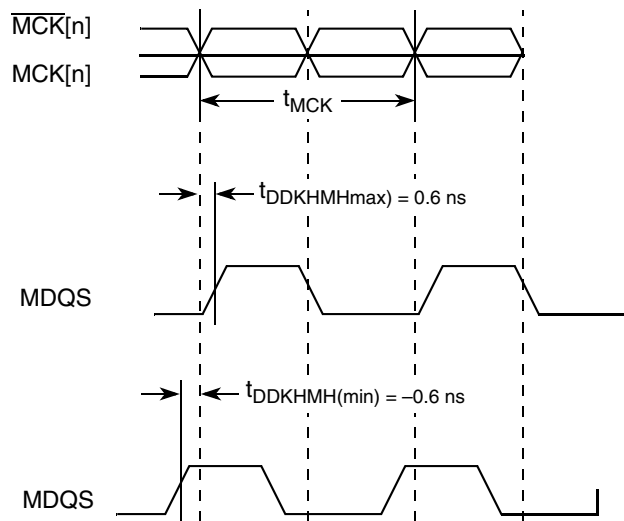
**Figure 6. Timing Diagram for t_{DDKHHM}**

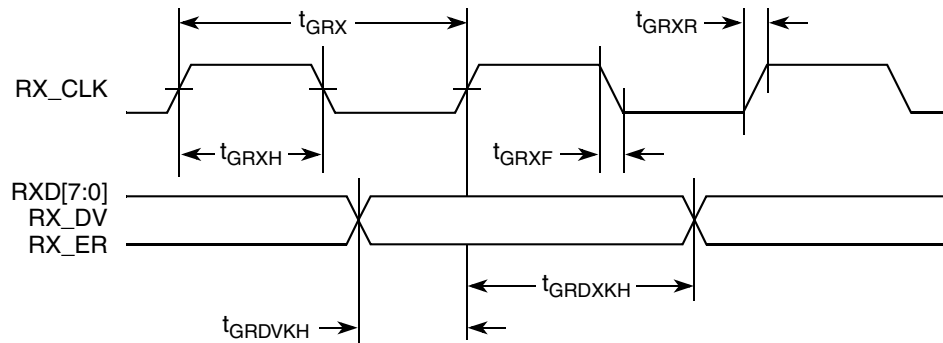
Table 26. GMII Receive AC Timing Specifications (continued)At recommended operating conditions with LV_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
RX_CLK clock rise (20%–80%)	t_{GRXR}	—	—	1.0	ns
RX_CLK clock fall time (80%–20%)	t_{GRXF}	—	—	1.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 10 shows the GMII receive AC timing diagram.

**Figure 10. GMII Receive AC Timing Diagram**

8.2.2 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.2.1 MII Transmit AC Timing Specifications

Table 27 provides the MII transmit AC timing specifications.

Table 27. MII Transmit AC Timing SpecificationsAt recommended operating conditions with LV_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns

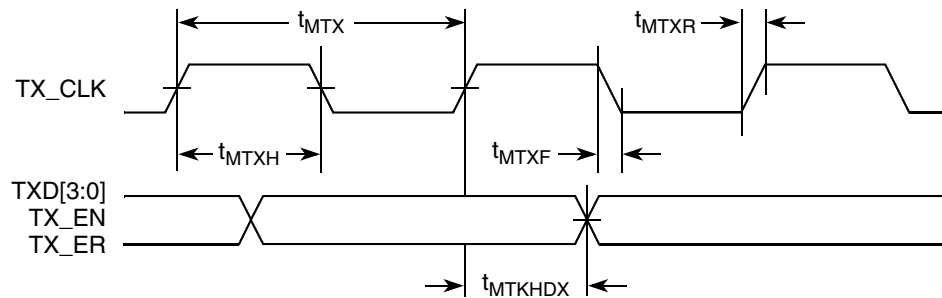
Table 27. MII Transmit AC Timing Specifications (continued)At recommended operating conditions with V_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
TX_CLK data clock rise (20%–80%)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall (80%–20%)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). In general, the clock reference symbol is based on two to three letters representing the clock of a particular function. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 11 shows the MII transmit AC timing diagram.

**Figure 11. MII Transmit AC Timing Diagram**

8.2.2.2 MII Receive AC Timing Specifications

Table 28 provides the MII receive AC timing specifications.

Table 28. MII Receive AC Timing SpecificationsAt recommended operating conditions with V_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns

Figure 21 through Figure 26 show the local bus signals.

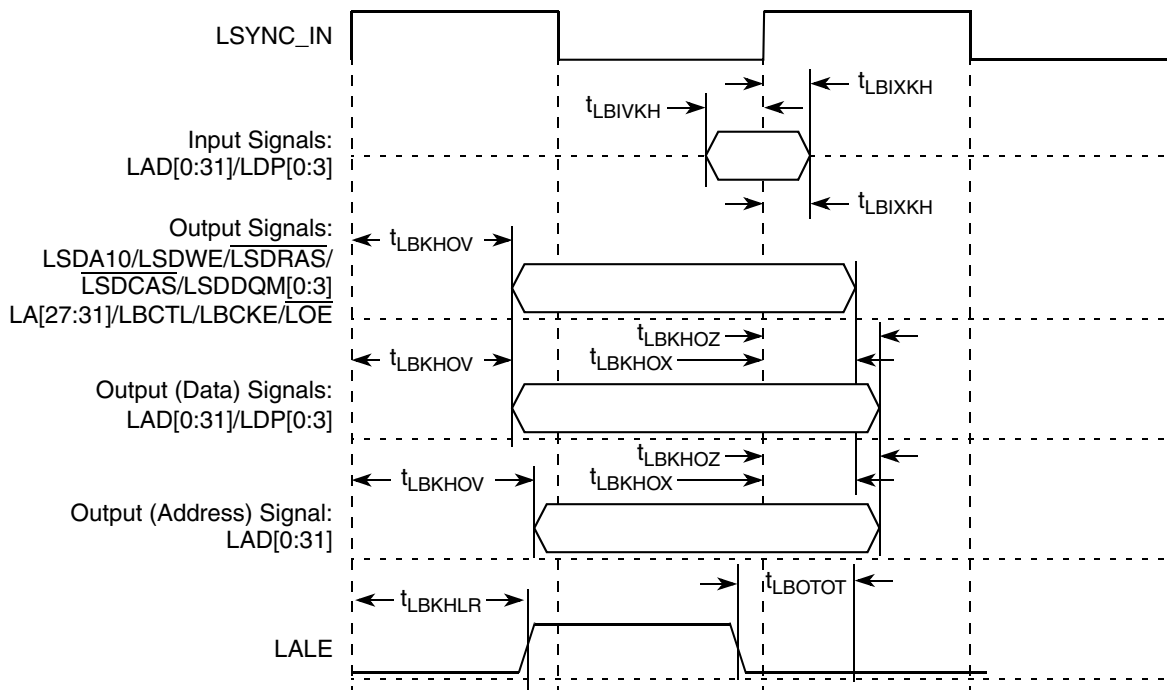


Figure 21. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

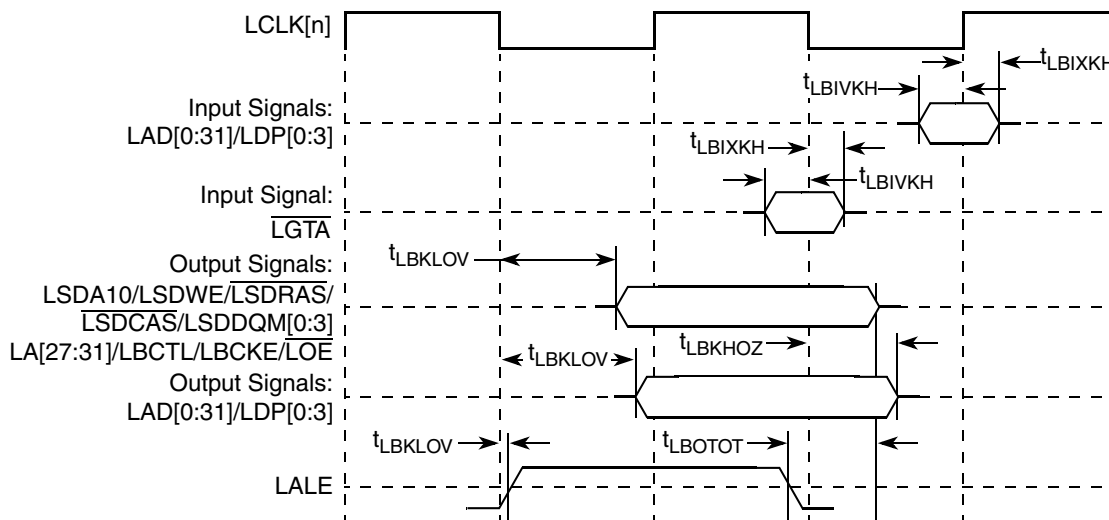


Figure 22. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

Table 47. Timer DC Electrical Characteristics (continued)

Parameter	Symbol	Condition	Min	Max	Unit
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

14.2 Timer AC Timing Specifications

Table 48 provides the timer input and output AC timing specifications.

Table 48. Timers Input AC Timing Specifications¹

Parameter	Symbol ²	Min	Unit
Timers inputs—minimum pulse width	t_{TIWID}	20	ns

Notes:

- Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.
- Timer inputs and outputs are asynchronous to any visible clock. Timer outputs should be synchronized before use by external synchronous logic. Timer inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

15 GPIO

This section describes the DC and AC electrical specifications for the GPIO.

15.1 GPIO DC Electrical Characteristics

Table 49 provides the DC electrical characteristics for the MPC8349EA GPIO.

Table 49. GPIO DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	−0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MBA[2]	H4	O	GV _{DD}	—
MDIC0	AB1	I/O	—	9
MDIC1	AA1	I/O	—	9
Local Bus Controller Interface				
LAD[0:31]	AM13, AP13, AL14, AM14, AN14, AP14, AK15, AJ15, AM15, AN15, AP15, AM16, AL16, AN16, AP16, AL17, AM17, AP17, AK17, AP18, AL18, AM18, AN18, AP19, AN19, AM19, AP20, AK19, AN20, AL20, AP21, AN21	I/O	OV _{DD}	—
LDP[0]/CKSTOP_OUT	AM21	I/O	OV _{DD}	—
LDP[1]/CKSTOP_IN	AP22	I/O	OV _{DD}	—
LDP[2]/LCS[4]	AN22	I/O	OV _{DD}	—
LDP[3]/LCS[5]	AM22	I/O	OV _{DD}	—
LA[27:31]	AK21, AP23, AN23, AP24, AK22	O	OV _{DD}	—
LCS[0:3]	AN24, AL23, AP25, AN25	O	OV _{DD}	—
LWE[0:3]/LSDDQM[0:3]/LBS[0:3]	AK23, AP26, AL24, AM25	O	OV _{DD}	—
LBCTL	AN26	O	OV _{DD}	—
LALE	AK24	O	OV _{DD}	—
LGPL0/LSDA10/cfg_reset_source0	AP27	I/O	OV _{DD}	—
LGPL1/LSDWE/cfg_reset_source1	AL25	I/O	OV _{DD}	—
LGPL2/LSDRAS/LOE	AJ24	O	OV _{DD}	—
LGPL3/LSDCAS/cfg_reset_source2	AN27	I/O	OV _{DD}	—
LGPL4/LGT/LUPWAIT/LPBSE	AP28	I/O	OV _{DD}	12
LGPL5/cfg_clkin_div	AL26	I/O	OV _{DD}	—
LCKE	AM27	O	OV _{DD}	—
LCLK[0:2]	AN28, AK26, AP29	O	OV _{DD}	—
LSYNC_OUT	AM12	O	OV _{DD}	—
LSYNC_IN	AJ10	I	OV _{DD}	—
General Purpose I/O Timers				
GPIO1[0]/DMA_DREQ0/GTM1_TIN1/GTM2_TIN2	F24	I/O	OV _{DD}	—
GPIO1[1]/DMA_DACK0/GTM1_TGATE1/GTM2_TGATE2	E24	I/O	OV _{DD}	—

As shown in [Figure 41](#), the primary clock input (frequency) is multiplied up by the system phase-locked loop (PLL) and the clock unit to create the coherent system bus clock (*csb_clk*), the internal clock for the DDR controller (*ddr_clk*), and the internal clock for the local bus interface unit (*lbiu_clk*).

The *csb_clk* frequency is derived from a complex set of factors that can be simplified into the following equation:

$$csb_clk = \{PCI_SYNC_IN \times (1 + CFG_CLKIN_DIV)\} \times SPMF$$

In PCI host mode, $PCI_SYNC_IN \times (1 + CFG_CLKIN_DIV)$ is the CLKIN frequency.

The *csb_clk* serves as the clock input to the e300 core. A second PLL inside the e300 core multiplies the *csb_clk* frequency to create the internal clock for the e300 core (*core_clk*). The system and core PLL multipliers are selected by the SPMF and COREPLL fields in the reset configuration word low (RCWL), which is loaded at power-on reset or by one of the hard-coded reset options. See the chapter on reset, clocking, and initialization in the *MPC8349EA Reference Manual* for more information on the clock subsystem.

The internal *ddr_clk* frequency is determined by the following equation:

$$ddr_clk = csb_clk \times (1 + RCWL[DDRCM])$$

ddr_clk is not the external memory bus frequency; *ddr_clk* passes through the DDR clock divider ($\div 2$) to create the differential DDR memory bus clock outputs (MCK and \overline{MCK}). However, the data rate is the same frequency as *ddr_clk*.

The internal *lbiu_clk* frequency is determined by the following equation:

$$lbiu_clk = csb_clk \times (1 + RCWL[LBIUCM])$$

lbiu_clk is not the external local bus frequency; *lbiu_clk* passes through the LBIU clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LBIU clock divider ratio is controlled by LCCR[CLKDIV].

In addition, some of the internal units may have to be shut off or operate at lower frequency than the *csb_clk* frequency. Those units have a default clock ratio that can be configured by a memory-mapped register after the device exits reset. [Table 56](#) specifies which units have a configurable clock frequency.

Table 56. Configurable Clock Units

Unit	Default Frequency	Options
TSEC1	<i>csb_clk</i> /3	Off, <i>csb_clk</i> , <i>csb_clk</i> /2, <i>csb_clk</i> /3
TSEC2, I ² C1	<i>csb_clk</i> /3	Off, <i>csb_clk</i> , <i>csb_clk</i> /2, <i>csb_clk</i> /3
Security core	<i>csb_clk</i> /3	Off, <i>csb_clk</i> , <i>csb_clk</i> /2, <i>csb_clk</i> /3
USB DR, USB MPH	<i>csb_clk</i> /3	Off, <i>csb_clk</i> , <i>csb_clk</i> /2, <i>csb_clk</i> /3
PCI1, PCI2 and DMA complex	<i>csb_clk</i>	Off, <i>csb_clk</i>

Table 58. System PLL Multiplication Factors (continued)

RCWL[SPMF]	System PLL Multiplication Factor
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11
1100	× 12
1101	× 13
1110	× 14
1111	× 15

As described in [Section 19, “Clocking,”](#) the LBIUCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). [Table 59](#) and [Table 60](#) show the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 59. CSB Frequency Options for Host Mode

CFG_CLKIN_DIV at Reset ¹	SPMF	<i>csb_clk</i> : Input Clock Ratio ²	Input Clock Frequency (MHz) ²			
			16.67	25	33.33	66.67
			<i>csb_clk</i> Frequency (MHz)			
Low	0010	2 : 1				133
Low	0011	3 : 1				100
Low	0100	4 : 1				133
Low	0101	5 : 1				166
				100	133	266
				125	166	333

Table 60. CSB Frequency Options for Agent Mode (continued)

CFG_CLKIN_DIV at Reset ¹	SPMF	csb_clk : Input Clock Ratio ²	Input Clock Frequency (MHz) ²			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0110	6 : 1	100	150	200	
Low	0111	7 : 1	116	175	233	
Low	1000	8 : 1	133	200	266	
Low	1001	9 : 1	150	225	300	
Low	1010	10 : 1	166	250	333	
Low	1011	11 : 1	183	275		
Low	1100	12 : 1	200	300		
Low	1101	13 : 1	216	325		
Low	1110	14 : 1	233			
Low	1111	15 : 1	250			
Low	0000	16 : 1	266			
High	0010	4 : 1		100	133	266
High	0011	6 : 1	100	150	200	
High	0100	8 : 1	133	200	266	
High	0101	10 : 1	166	250	333	
High	0110	12 : 1	200	300		
High	0111	14 : 1	233			
High	1000	16 : 1	266			

¹ CFG_CLKIN_DIV doubles *csb_clk* if set high.

² CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

19.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 61 shows the encodings for RCWL[COREPLL]. COREPLL values that are not listed in Table 61 should be considered as reserved.

NOTE

Core VCO frequency = core frequency × VCO divider

VCO divider must be set properly so that the core VCO frequency is in the range of 800–1800 MHz.

Table 63. Package Thermal Characteristics for TBGA (continued)

Characteristic	Symbol	Value	Unit	Notes
Junction-to-package natural convection on top	Ψ_{JT}	1	°C/W	6

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal, 1 m/s is approximately equal to 200 linear feet per minute (LFM).
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

20.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$ where $P_{I/O}$ is the power dissipation of the I/O drivers. See [Table 5](#) for I/O power dissipation values.

20.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J , can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Generally, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

20.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance ($^{\circ}\text{C}/\text{W}$)

$R_{\theta JC}$ = junction-to-case thermal resistance ($^{\circ}\text{C}/\text{W}$)

$R_{\theta CA}$ = case-to-ambient thermal resistance ($^{\circ}\text{C}/\text{W}$)

$R_{\theta JC}$ is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

The thermal performance of devices with heat sinks has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, air flow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

Table 64 shows heat sink thermal resistance for TBGA of the MPC8349EA.

Table 64. Heat Sink and Thermal Resistance of MPC8349EA (TBGA)

Heat Sink Assuming Thermal Grease	Air Flow	35 × 35 mm TBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	10
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	6.5
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	5.6
AAVID 31 × 35 × 23 mm pin fin	Natural convection	8.4
AAVID 31 × 35 × 23 mm pin fin	1 m/s	4.7
AAVID 31 × 35 × 23 mm pin fin	2 m/s	4
Wakefield, 53 × 53 × 25 mm pin fin	Natural convection	5.7
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	3.5
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	2.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convection	6.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	1 m/s	4.1
MEI, 75 × 85 × 12 no adjacent board, extrusion	2 m/s	2.8
MEI, 75 × 85 × 12 mm, adjacent board, 40 mm side bypass	1 m/s	3.1

Accurate thermal design requires thermal modeling of the application environment using computational fluid dynamics software which can model both the conduction cooling and the convection cooling of the air moving through the application. Simplified thermal models of the packages can be assembled using the junction-to-case and junction-to-board thermal resistances listed in the thermal resistance table. More detailed thermal models can be made available on request.

The Bergquist Company
 18930 West 78th St.
 Chanhassen, MN 55317
 Internet: www.bergquistcompany.com

800-347-4572

20.3 Heat Sink Attachment

When heat sinks are attached, an interface material is required, preferably thermal grease and a spring clip. The spring clip should connect to the printed-circuit board, either to the board itself, to hooks soldered to the board, or to a plastic stiffener. Avoid attachment forces that can lift the edge of the package or peel the package from the board. Such peeling forces reduce the solder joint lifetime of the package. The recommended maximum force on the top of the package is 10 lb force (4.5 kg force). Any adhesive attachment should attach to painted or plastic surfaces, and its performance should be verified under the application requirements.

20.3.1 Experimental Determination of the Junction Temperature with a Heat Sink

When a heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimize the size of the clearance to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_J = junction temperature (°C)

T_C = case temperature of the package (°C)

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

P_D = power dissipation (W)

21 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8349EA.

21.1 System Clocking

The MPC8349EA includes two PLLs:

1. The platform PLL generates the platform clock from the externally supplied CLKIN input. The frequency ratio between the platform and CLKIN is selected using the platform PLL ratio configuration bits as described in [Section 19.1, “System PLL Configuration.”](#)

have a low ESR (equivalent series resistance) rating to ensure the quick response time. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors are 100–330 μF (AVX TPS tantalum or Sanyo OSCON).

21.4 Connection Recommendations

To ensure reliable operation, connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD} , GV_{DD} , or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD} , GV_{DD} , LV_{DD} , OV_{DD} , and GND pins of the MPC8349EA.

21.5 Output Buffer DC Impedance

The MPC8349EA drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then the value of each resistor is varied until the pad voltage is $\text{OV}_{\text{DD}}/2$ (see Figure 43). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $\text{OV}_{\text{DD}}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N) \div 2$.

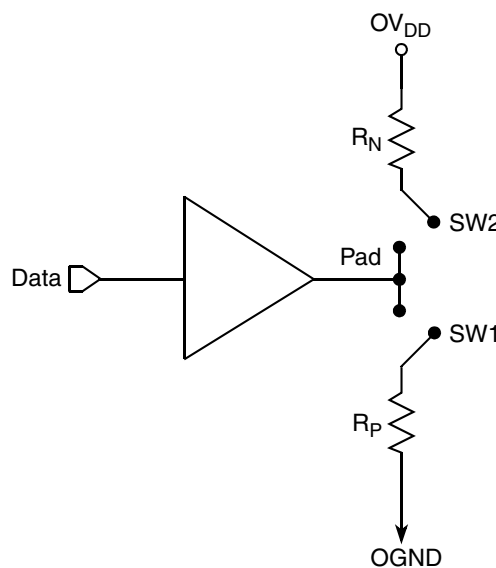


Figure 43. Driver Impedance Measurement

Two measurements give the value of this resistance and the strength of the driver current source. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{\text{source}} \times I_{\text{source}}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is

$V_2 = (1 \div (1/R_1 + 1/R_2)) \times I_{\text{source}}$. Solving for the output impedance gives $R_{\text{source}} = R_{\text{term}} \times (V_1 \div V_2 - 1)$. The drive current is then $I_{\text{source}} = V_1 \div R_{\text{source}}$.

Table 65 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD} , nominal OV_{DD} , 105°C.

Table 65. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI Signals (Not Including PCI Output Clocks)	PCI Output Clocks (Including PCI_SYNC_OUT)	DDR DRAM	Symbol	Unit
R_N	42 Target	25 Target	42 Target	20 Target	Z_0	W
R_P	42 Target	25 Target	42 Target	20 Target	Z_0	W
Differential	NA	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See [Table 1](#), $T_j = 105^\circ\text{C}$.

21.6 Configuration Pin Multiplexing

The MPC8349EA power-on configuration options can be set through external pull-up or pull-down resistors of 4.7 k Ω on certain output pins (see the customer-visible configuration pins). These pins are used as output only pins in normal operation.

However, while $\overline{\text{HRESET}}$ is asserted, these pins are treated as inputs, and the value on these pins is latched when $\overline{\text{PORESET}}$ deasserts. Then the input receiver is disabled and the I/O circuit takes on its normal function. Careful board layout with stubless connections to these pull-up/pull-down resistors coupled with the large value of the pull-up/pull-down resistor should minimize the disruption of signal quality or speed for the output pins.

21.7 Pull-Up Resistor Requirements

The MPC8349EA requires high resistance pull-up resistors (10 k Ω is recommended) on open-drain pins, including I²C pins, and IPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, refer to application note AN2931, “PowerQUICC Design Checklist.”

22 Ordering Information

This section presents ordering information for the device discussed in this document, and it shows an example of how the parts are marked.

NOTE

The information in this document is accurate for revision 3.x silicon and later (in other words, for orderable part numbers ending in A or B). For information on revision 1.1 silicon and earlier versions, see the *MPC8349E PowerQUICC II Pro Integrated Host Processor Hardware Specifications* (Document Order No. MPC8349EEC).